

WHAT IS CLAIMED IS:

1. A thin film diode panel comprising:
 - a insulating substrate;
 - a first and second gate lines formed on the insulating substrate;
 - 5 a reflection electrode formed on the insulating substrate;
 - a transmission electrode formed on the insulating substrate;
 - a first MIM diode formed on the insulating substrate and connecting the first gate line and the reflection electrode;
 - a second MIM diode formed on the insulating substrate and
 - 10 connecting the second gate line and the reflection electrode;
 - a third MIM diode formed on the insulating substrate and connecting the first gate line and the transmission electrode; and
 - a fourth MIM diode formed on the insulating substrate and connecting the second gate line and the transmission electrode,
 - 15 wherein at least one of the first to fourth MIM diodes has a substantially different current-voltage (I-V) characteristic from the others.
2. The thin film diode panel of claim 1, wherein the first and fourth MIM diodes have a substantially same I-V characteristic and the second and third MIM diodes have a substantially same I-V characteristic.
- 20 3. The thin film diode panel of claim 2, wherein the first and fourth MIM diodes permit a larger current than the second and third MIM diode

under a same driving voltage.

4. The thin film diode panel of claim 1, wherein the reflection electrode is made of a material including at least one of the Al and Ag, and the transmission electrode is made of a material including at least one of the ITO and IZO.

5. A thin film diode panel comprising:

- a insulating substrate;
- a first gate line formed on the insulating substrate and including a first input electrode;
- 10 a second gate line formed on the insulating substrate and including a second input electrode;
- a reflection electrode formed on the insulating substrate including a first and second contact portions;
- a transmission electrode formed on the insulating substrate
- 15 including a third and fourth contact portions;
- insulating layers formed on the first input electrode and the first and third contact portions and on the second input electrode and the second and fourth contact portions;
- a first floating electrode formed on the insulating layer and
- 20 intersecting the first input electrode and the first and third contact portions;
- and

a second floating electrode formed on the insulating layer and intersecting the second input electrode and the second and fourth contact portions,

wherein the overlapping area of the first floating electrode and the first contact portion is substantially different from the overlapping area of the first floating electrode and the third contact portion.

6. The thin film diode panel of claim 5, wherein the overlapping area of the second floating electrode and the second contact portion is substantially different from the overlapping area of the second floating electrode and the fourth contact portion.

7. The thin film diode panel of claim 6, wherein the overlapping area of the first floating electrode and the first contact portion is substantially the same as the overlapping area of the second floating electrode and the fourth contact portion, and

the overlapping area of the first floating electrode and the third contact portion is substantially the same as the overlapping area of the second floating electrode and the second contact portion.

8. The thin film diode panel of claim 7, wherein the overlapping area of the first floating electrode and the first contact portion is substantially narrower than the overlapping area of the first floating electrode and the third contact portion..

9. The thin film diode panel of claim 5, further comprising a first and second redundant gate lines respectively formed on the first and second gate lines.